## 1 Characteristics

Table	2. Absolute maximum ratings (limiting values; T	<sub>j</sub> = 25 °C, unless oth	erwise spec	ified)

Symbol	Parameter	Value	Unit			
I <sub>T(RMS)</sub>	On-state rms current (full sine wave)		T <sub>c</sub> = 86 °C	16	А	
1	Non repetitive surge peak on-state current (full	F = 50 Hz	t <sub>p</sub> = 20 ms	120	А	
ITSM	cycle, T <sub>j</sub> initial = 25 °C)	F = 60 Hz	t <sub>p</sub> = 16.7 ms	126	~	
l²t	$l^2t$ Value for fusing $t_p = 10 \text{ ms}$				A²s	
dl/dt	$ \begin{array}{ c c c } \hline Critical rate of rise of on-state current I_G = 2 \times I_{GT} \\ t_r \leq 100 \text{ ns} \end{array}  F = 60 \text{ Hz}  T_j = 125 \text{ °C} \\ \hline \end{array} $		50	A/µs		
V <sub>DSM</sub> / V <sub>RSM</sub>	Non repetitive surge peak off-state voltage $t_p = 10 \text{ ms}$ $T_j = 25 \text{ °C}$		V <sub>DRM</sub> /V <sub>RRM</sub> + 100	V		
I <sub>GM</sub>	Peak gate current $t_p = 20 \ \mu s$ $T_j = 125 \ ^{\circ}C$				А	
P <sub>G(AV)</sub>	Average gate power dissipation $T_j = 125 \text{ °C}$				W	
T <sub>stg</sub>	Storage junction temperature range				°C	
Тj	Operating junction temperature range	- 40 to + 125	°C			

Symbol	Test conditions	Our dramt		T16xxT			-	Unit
Symbol	Test conditions	Quadrant		T1610T	T1620T	T1635T	Unit	
I <sub>GT</sub> <sup>(1)</sup>	$V_{\rm D} = 12  \text{V}  \text{R}_{\rm I} = 30  \text{W}$	1 - 11 - 111	MAX.	10	20	35	mA	
'GT `´	$v_{\rm D} = 12 v K_{\rm L} = 50 v v$	IV					ШA	
V <sub>GT</sub>	$V_D = V_{DRM}, R_L = 3.3 \text{ kW},$ $T_j = 25 \text{ °C}$	ALL	MAX.		1.3		V	
V <sub>GD</sub>	$V_{D} = V_{DRM}, R_{L} = 3.3 \text{ kW},$ $T_{j} = 125 \text{ °C}$	ALL	MIN.	0.2		V		
I <sub>H</sub> <sup>(2)</sup>	I <sub>T</sub> = 500 mA		MAX.	12	25	40	mA	
		1 - 111		20	35	50	mA	
۱ <sub>L</sub>	$I_{G} = 1.2 I_{GT}$	IV	MAX.					
		II		30	40	80		
dV/dt <sup>(2)</sup>	V <sub>D</sub> = 67% V <sub>DRM.</sub> gate open	T <sub>j</sub> = 125 °C	= 125 °C MIN.		1000	2000	\//ue	
uviu	VD - 07 % VDRM, gate open	$T_j = 150 \ ^{\circ}C^{(3)}$	IVIIIN.	20	500	1000	V/µs	
	(dV/dt)c = 0.1 V/µs			8				
	(dV/dt)c = 10 V/µs	T <sub>j</sub> = 125 °C		4				
(di/dt)c <sup>(2)</sup>	Without snubber		MIN.		6	16	A/ms	
	(dV/dt)c = 0.1 V/µs		IVIIIN.	3			AVIIIS	
	(dV/dt)c = 10 V/µs	$T_j = 150 \ ^{\circ}C^{(3)}$		1				
	Without snubber				3	12		

Table 3. Electrical characteristics (T<sub>i</sub> = 25 °C, unless otherwise specified)

1. minimum  $I_{GT}$  is guaranted at 5% of  $I_{GT}$  max.

2. for both polarities of A2 referenced to A1.

3. derating information for excess temperature above  $T_i$  max.

#### Table 4. Static characteristics

Symbol	Test conditions				Unit
V <sub>T</sub> <sup>(1)</sup>	I <sub>TM</sub> = 22.6 A, t <sub>p</sub> = 380 μs	T <sub>j</sub> = 25 °C	MAX.	1.55	V
V <sub>TO</sub> <sup>(1)</sup>	Threshold voltage	T <sub>j</sub> = 125 °C	MAX.	0.85	V
R <sub>D</sub> <sup>(1)</sup>	Dynamic resistance	T <sub>j</sub> = 125 °C	MAX.	30	mΩ
		T <sub>j</sub> = 25 °C	MAX.	5	μA
	$V_{DRM} = V_{RRM}$	T <sub>j</sub> = 125 °C	IVIAA.	1	
IRRM	$V_{D} = 0.9 \times V_{DRM}$	$T_j = 150 \ ^{\circ}C^{(2)}$	TYP.	1.9	mA

1. for both polarities of A2 referenced to A1.

2. derating information for excess temperature above  $T_j$  max.



Symbol	Parameter	Value	Unit					
R <sub>th(j-c)</sub>	Junction to case (AC)	2.1	°C/W					
R <sub>th(j-a)</sub>	Junction to ambient (DC)	60	°C/W					

### Table 5. Thermal resistance

# Figure 1. Maximum power dissipation versus rms on-state current (full cycle)

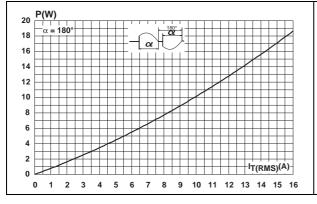


Figure 3. On-state rms current versus ambient temperature

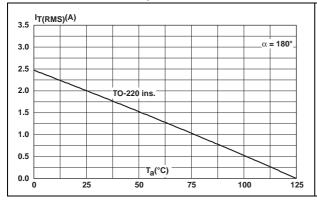
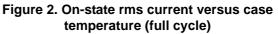


Figure 5. On state characteristics (maximum values)



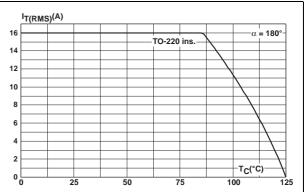


Figure 4. Relative variation of thermal impedance versus pulse duration

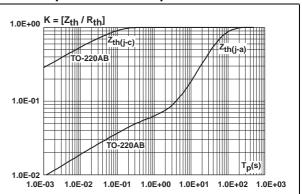
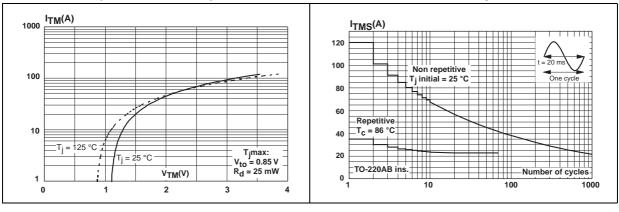
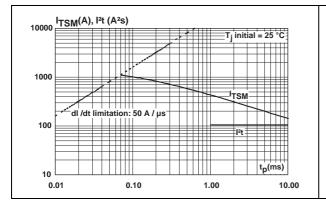


Figure 6. Surge peak on state current versus number of cycles

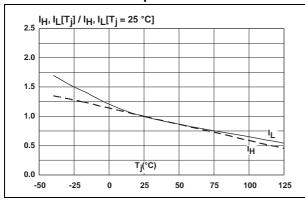




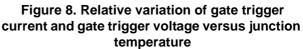
### Figure 7. Non repetitive surge peak on state current for a sinusoidal



#### Figure 9. Relative variation of holding current and latching current versus junction temperature



### Figure 11. Relative variation of critical rate of decrease of main current versus junction temperature



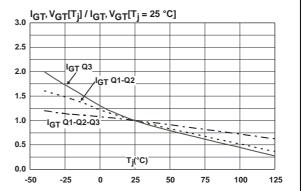


Figure 10. Relative variation of critical rate of decrease of main current versus junction temperature

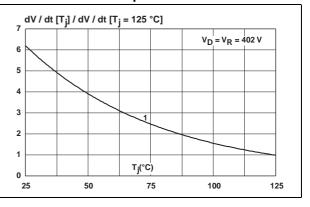
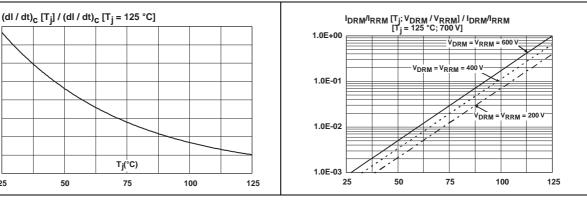


Figure 12. Leakage current versus junction temperature for different values of blocking voltage (typical values)





8

7

6

5 Λ 3

2 1

0

25

## 2 Ordering information scheme

Figure 13. Ordering information scheme

	т	16	10	т	-	6	ļ
TRIAC							
Current							
16 = 16 A							
Sensitivity							
10 = 10 mA							
20 = 20 mA							
35 = 35 mA							
Application specific							
Voltage							
6 = 600 V							
Package							
I = TO-220AB-Ins.							



### 3 Package mechanical data

- Epoxy meets UL94, V0
- Lead-free packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <u>www.st.com</u>. ECOPACK<sup>®</sup> is an ST trademark.

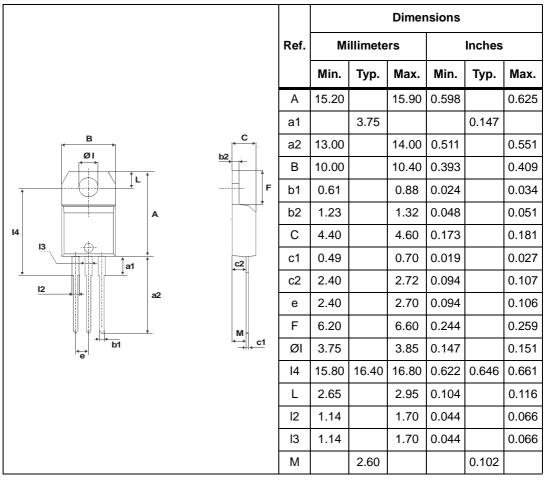


Table 6. TO-220AB insulated dimensions



## 4 Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode	
T1610T-6I	T1610T-6I					
T1620T-6I	T1620T-6I	TO-220AB ins.	2.3 g	50	Tube	
T1635T-6I	T1635T-6I					

Table 7. Ordering information

### 5 Revision history

Date	Revision	Changes
03-Dec-2009	1	Initial release.
18-Jan-2010 2 L		Updated pag.1.
19-Jun-2014 3 Updated features in cover page.		Updated features in cover page.

Table 8. Document revision history



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